

General Purpose Transistors

NPN Silicon

BC846ALT1G Series

Features

- Moisture Sensitivity Level: 1
- ESD Rating Human Body Model: > 4000 V
 - Machine Model: > 400 V
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Collector-Emitter Voltage	BC846 BC847, BC850 BC848, BC849	V _{CEO}	65 45 30	Vdc
Collector-Base Voltage	BC846 BC847, BC850 BC848, BC849	V _{CBO}	80 50 30	Vdc
Emitter-Base Voltage	BC846 BC847, BC850 BC848, BC849	V _{EBO}	6.0 6.0 5.0	Vdc
Collector Current – Contin	uous	I _C	100	mAdc

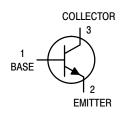
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) T _A = 25°C Derate above 25°C	P _D	225	mW mW/°C
Derate above 23 C		1.0	IIIVV/ C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ heta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T _A = 25°C Derate above 25°C	P _D	300	mW mW/°C
Derate above 25 C		2.4	IIIVV/ C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ hetaJA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C

1

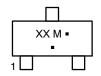
- 1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- 2. Alumina = 0.4 \times 0.3 \times 0.024 in 99.5% alumina.





SOT-23 CASE 318 STYLE 6

MARKING DIAGRAM



XX = Device CodeM = Date Code*= Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

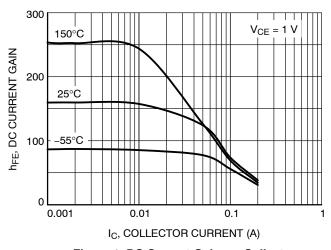
See detailed ordering and shipping information in the package dimensions section on page 12 of this data sheet.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic			Min	Тур	Max	Unit
OFF CHARACTERISTICS			•	•	•	•
Collector – Emitter Breakdown Voltage (I _C = 10 mA)	BC846A, B, C BC847A, B, C, BC850B, C BC848A, B, C, BC849B, C	V _{(BR)CEO}	65 45 30	- - -	- - -	V
Collector – Emitter Breakdown Voltage ($I_C = 10 \mu A, V_{EB} = 0$)	BC846A, B, C BC847A, B, C BC850B, C BC848A, B, C, BC849B, C	V _(BR) CES	80 50 30	- - -	- - -	V
Collector – Base Breakdown Voltage ($I_C = 10 \mu A$)	BC846A, B, C BC847A, B, C, BC850B, C BC848A, B, C, BC849B, C	V _{(BR)CBO}	80 50 30	- - -	- - -	٧
Emitter – Base Breakdown Voltage ($I_E = 1.0 \mu A$)	BC846A, B, C BC847A, B, C, BC850B, C BC848A, B, C, BC849B, C	V _{(BR)EBO}	6.0 6.0 5.0	- - -	- - -	٧
Collector Cutoff Current (V _{CB} = 30 V) (V _{CB} = 30 V, T _A = 150°C)		I _{CBO}	- -	- -	15 5.0	nA μA
ON CHARACTERISTICS						
DC Current Gain ($I_C = 10 \mu A$, $V_{CE} = 5.0 V$)	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC846C, BC847C, BC848C	h _{FE}	- - -	90 150 270	- - -	-
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC846A, BC847A, BC848A BC846B, BC847B, BC848B, BC849B, BC850B		110 200	180 290	220 450	
BC846C, BC847C, BC848C, BC849C, BC850C			420	520	800	
Collector – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)			-	_ _	0.25 0.6	V
Base – Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA)			- -	0.7 0.9	- -	V
Base – Emitter Voltage (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 10 mA, V_{CE} = 5.0 V)			580 -	660 -	700 770	mV
SMALL-SIGNAL CHARACTERISTICS						
Current – Gain – Bandwidth Product ($I_C = 10$ mA, $V_{CE} = 5.0$ Vdc, $f = 100$ MHz)		f _T	100	-	_	MHz
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)			_	-	4.5	pF
Noise Figure (I_C = 0.2 mA, V_{CE} = 5.0 Vdc, R_S = 2.0 k Ω , BC846A,B,C, BC847A,B,C, BC848A,B,C f = 1.0 kHz, BW = 200 Hz) BC849B,C, BC850B,C			- -	- -	10 4.0	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BC846A, BC847A, BC848A, SBC846A



300 150°C VCE = 5 V VCE = 5 V 200 25°C 100 --55°C 0 0.001 0.01 1c, COLLECTOR CURRENT (A)

Figure 1. DC Current Gain vs. Collector Current

Figure 2. DC Current Gain vs. Collector Current

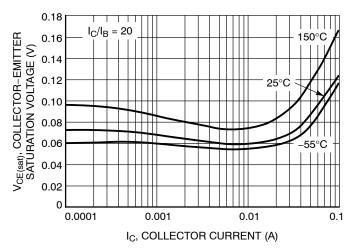


Figure 3. Collector Emitter Saturation Voltage vs. Collector Current

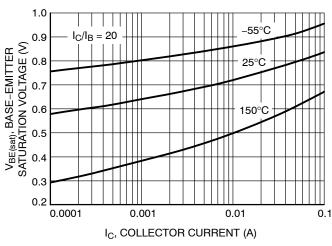


Figure 4. Base Emitter Saturation Voltage vs.
Collector Current

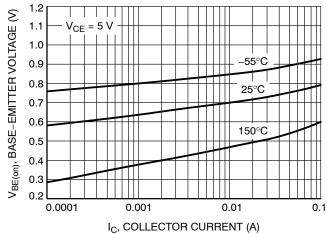
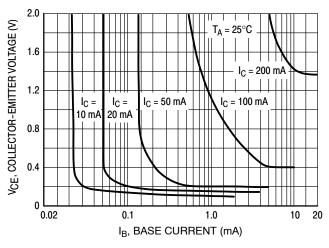


Figure 5. Base Emitter Voltage vs. Collector Current

BC846A, BC847A, BC848A, SBC846A



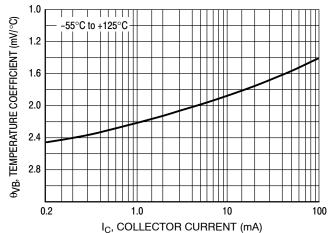
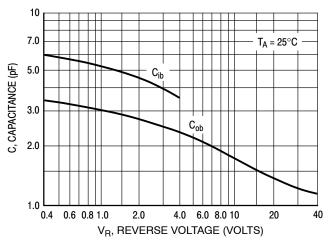


Figure 6. Collector Saturation Region

Figure 7. Base-Emitter Temperature Coefficient





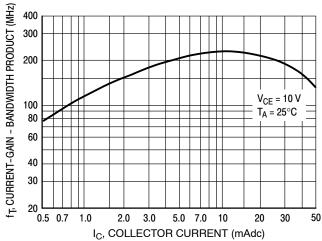


Figure 9. Current-Gain - Bandwidth Product

BC846B, SBC846B

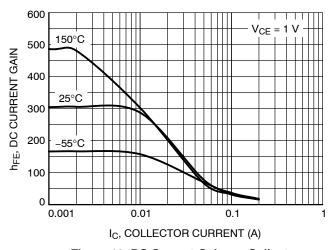


Figure 10. DC Current Gain vs. Collector Current

Figure 11. DC Current Gain vs. Collector Current

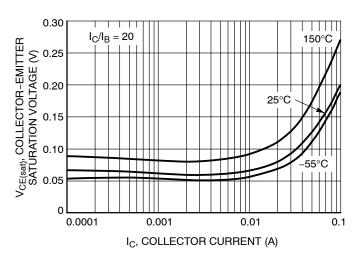


Figure 12. Collector Emitter Saturation Voltage vs. Collector Current

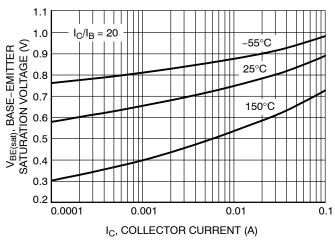


Figure 13. Base Emitter Saturation Voltage vs. Collector Current

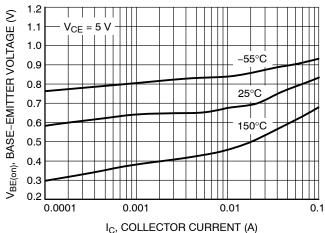
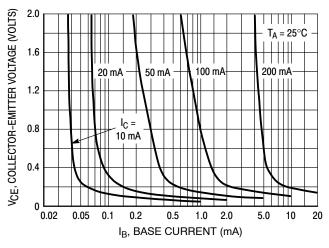


Figure 14. Base Emitter Voltage vs. Collector Current

BC846B, SBC846B



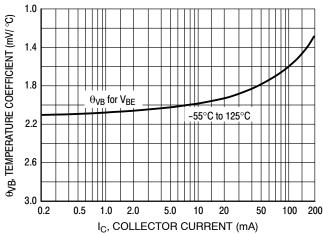


Figure 15. Collector Saturation Region

Figure 16. Base-Emitter Temperature Coefficient

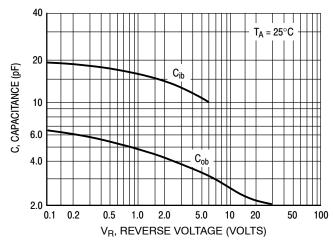


Figure 17. Capacitance

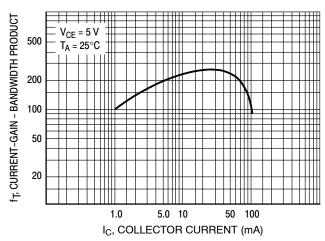
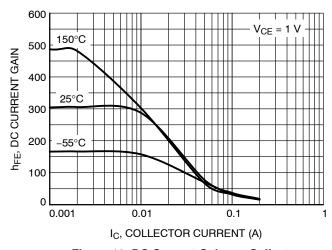


Figure 18. Current-Gain - Bandwidth Product

BC847B, BC848B, BC849B, BC850B, SBC847B, SBC848B



600 $V_{CE} = 5 V$ 150°C 500 h_{FE}, DC CURRENT GAIN 400 25°C 300 200 -55°C 100 0 0.001 0.01 0.1 I_C, COLLECTOR CURRENT (A)

Figure 19. DC Current Gain vs. Collector Current

Figure 20. DC Current Gain vs. Collector Current

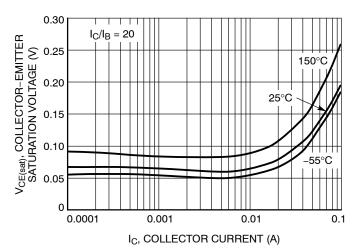
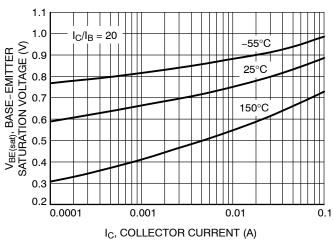


Figure 21. Collector Emitter Saturation Voltage vs. Collector Current





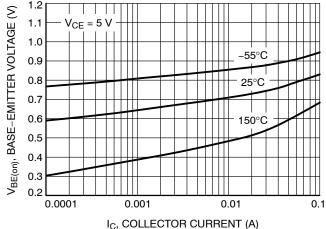


Figure 23. Base Emitter Voltage vs. Collector Current

BC847B, BC848B, BC849B, BC850B, SBC846B, SBC847B, SBC848B

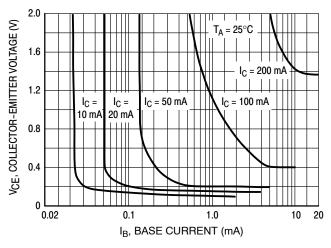


Figure 24. Collector Saturation Region

Figure 25. Base–Emitter Temperature Coefficient

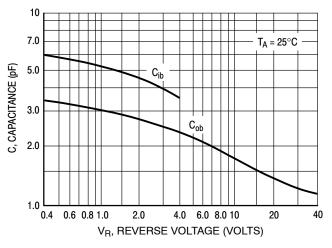


Figure 26. Capacitances

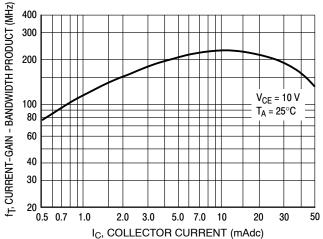
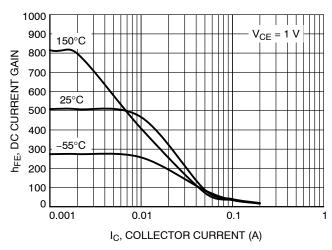


Figure 27. Current-Gain - Bandwidth Product

BC846C, BC847C, BC848C, BC849C, BC850C, SBC847C



1000 900 150°C V_{CE} 800 hFE, DC CURRENT GAIN 700 600 25°C 500 400 -55°C 300 200 100 0.001 0.01 0.1 IC, COLLECTOR CURRENT (A)

Figure 28. DC Current Gain vs. Collector Current

Figure 29. DC Current Gain vs. Collector Current

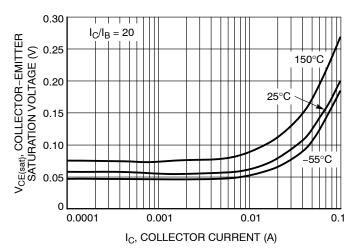


Figure 30. Collector Emitter Saturation Voltage vs. Collector Current

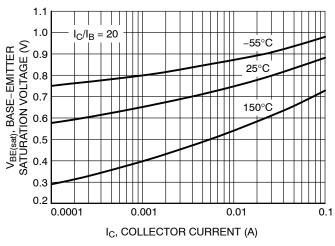


Figure 31. Base Emitter Saturation Voltage vs. Collector Current

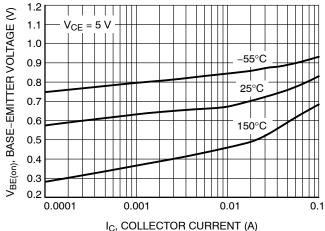


Figure 32. Base Emitter Voltage vs. Collector Current

BC846C, BC847C, BC848C, BC849C, BC850C, SBC847C

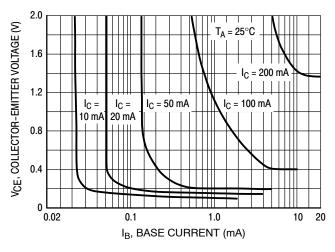
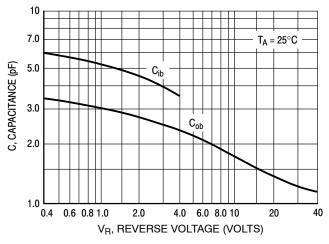


Figure 33. Collector Saturation Region

Figure 34. Base–Emitter Temperature Coefficient



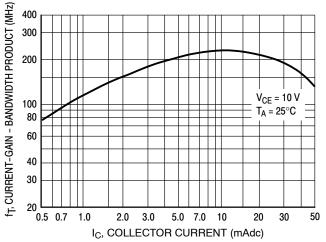


Figure 35. Capacitances

Figure 36. Current-Gain - Bandwidth Product

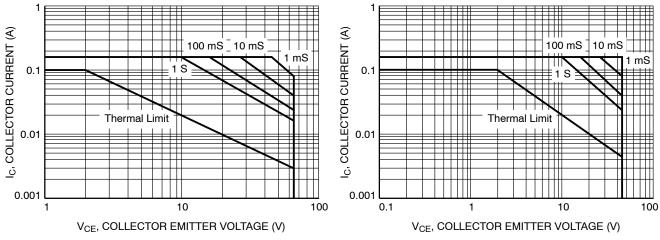


Figure 37. Safe Operating Area for BC846A, BC846B, BC846C

Figure 38. Safe Operating Area for BC847A, BC847B, BC847C, BC850B, BC850C

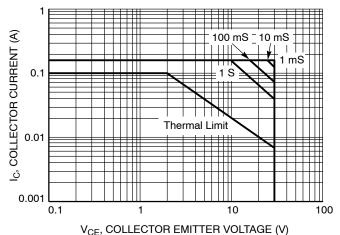


Figure 39. Safe Operating Area for BC848A, BC848B, BC848C, BC849B, BC849C

ORDERING INFORMATION

Device	Marking	Package	Shipping [†]		
BC846ALT1G					
SBC846ALT1G*	1A		3,000 / Tape & Reel		
BC846ALT3G			10,000 / Tape & Reel		
BC846BLT1G		1	2 000 / Tana & Baal		
SBC846BLT1G*	45		3,000 / Tape & Reel		
BC846BLT3G	1B		10 000 /T 0 D 1		
SBC846BLT3G*			10,000 / Tape & Reel		
BC846CLT1G	3C	1	3,000 / Tape & Reel		
BC847ALT1G			3,000 / Tape & Reel		
BC847ALT3G	1E		10,000 / Tape & Reel		
BC847BLT1G			0.000 /T 0.00 /		
SBC847BLT1G*			3,000 / Tape & Reel		
BC847BLT3G	1F				
NSVBC847BLT3G*			10,000 / Tape & Reel		
BC847CLT1G		1			
SBC847CLT1G*	1G		3,000 / Tape & Reel		
BC847CLT3G		SOT-23 (Pb-Free)	10,000 / Tape & Reel		
BC848ALT1G	1J	(. 5 5)	3,000 / Tape & Reel		
BC848BLT1G		1			
SBC848BLT1G*	1K		3,000 / Tape & Reel		
BC848BLT3G			10,000 / Tape & Reel		
BC848CLT1G			0.000 /T 0.D /		
NSVBC848CLT1G*	1L		3,000 / Tape & Reel		
BC848CLT3G			10,000 / Tape & Reel		
BC849BLT1G			0.000 /T 0 P I		
NSVBC849BLT1G*	2B		3,000 / Tape & Reel		
BC849BLT3G			10,000 / Tape & Reel		
BC849CLT1G			3,000 / Tape & Reel		
BC849CLT3G	2C		10,000 / Tape & Reel		
BC850BLT1G	0.5				
NSVBC850BLT1G*	2F		0.000 / Table 2. Dead		
BC850CLT1G	20		3,000 / Tape & Reel		
NSVBC850CLT1G*	2G				

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

DATE 30 JAN 2018

0.017

0.021

0.094

0.022

0.027

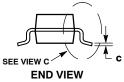
0.104

10°

SCALE 4:1 D Ε – 3X h **TOP VIEW**







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

PIN 1. RETURN

3. INPUT

3. ANODE

STYLE 28: PIN 1. ANODE 2. ANODE

2. OUTPUT

NOTES:

0.43

0.54

2.40

0.30

0.35

2.10

0°

ΗE

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS				INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Е	1.20	1.30	1.40	0.047	0.051	0.055
٩	1 78	1 90	2 04	0.070	0.075	0.080

0.55

0.69

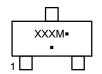
2.64

10° 0° **GENERIC MARKING DIAGRAM***

0.012

0.014

0.083



XXX = Specific Device Code

= Date Code

PIN 1. ANODE 2. CATHODE

3. GATE

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	N	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	N PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:

PIN 1. ANODE

ANODE

CATHODE

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repo Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.	
DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 1

PIN 1. GATE 2. DRAIN

3. SOURCE

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PIN 1. GATE

2. SOURCE

3. CATHODE

DRAIN

STYLE 27: PIN 1. CATHODE 2. CATHODE

PIN 1. CATHODE 2. ANODE

3. NO CONNECTION

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Europe, Middle East and Africa Technical Support:

Phone: 00421 33 790 2910

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